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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

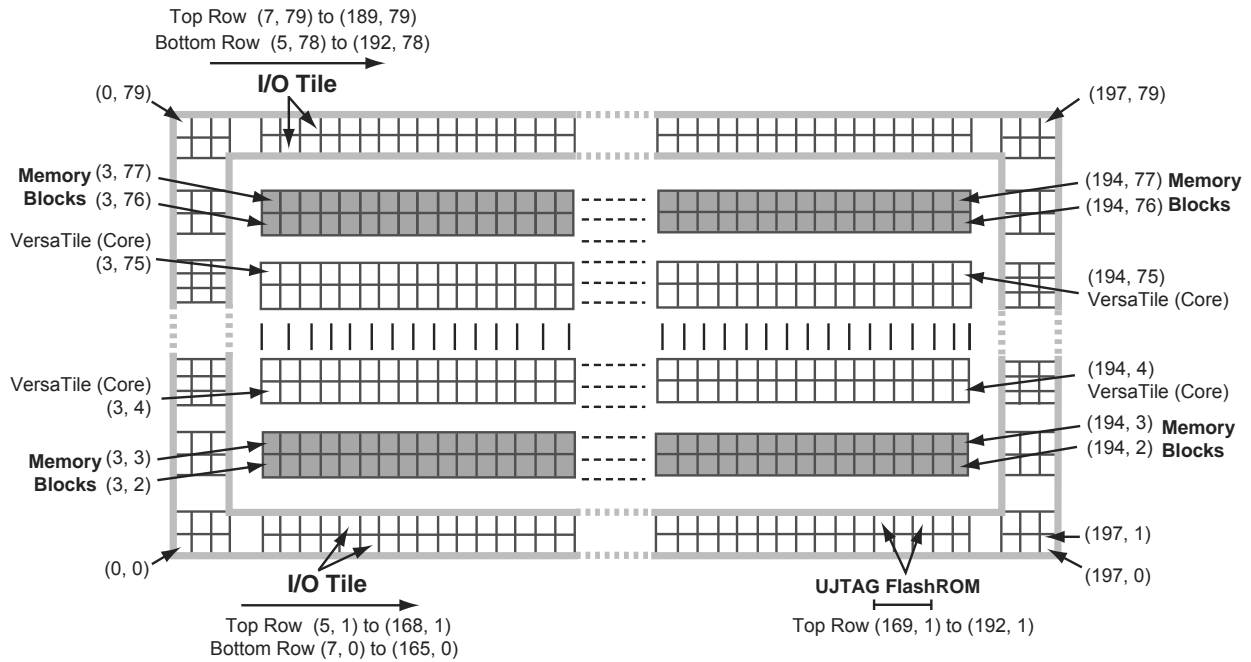
#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	49
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3pn030-zqng68i">https://www.e-xfl.com/product-detail/microchip-technology/a3pn030-zqng68i</a>

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**Table 1-4 • IGLOO nano and ProASIC3 nano Array Coordinates**

Device		VersaTiles		Memory Rows		Entire Die	
		Min.	Max.	Bottom	Top	Min.	Max.
IGLOO nano	ProASIC3 nano	(x, y)	(x, y)	(x, y)	(x, y)	(x, y)	(x, y)
AGLN010	A3P010	(0, 2)	(32, 5)	None	None	(0, 0)	(34, 5)
AGLN015	A3PN015	(0, 2)	(32, 9)	None	None	(0, 0)	(34, 9)
AGLN020	A3PN020	(0, 2)	32, 13)	None	None	(0, 0)	(34, 13)
AGLN060	A3PN060	(3, 2)	(66, 25)	None	(3, 26)	(0, 0)	(69, 29)
AGLN125	A3PN125	(3, 2)	(130, 25)	None	(3, 26)	(0, 0)	(133, 29)
AGLN250	A3PN250	(3, 2)	(130, 49)	None	(3, 50)	(0, 0)	(133, 49)



Note: The vertical I/O tile coordinates are not shown. West-side coordinates are {(0, 2) to (2, 2)} to {(0, 77) to (2, 77)}; east-side coordinates are {(195, 2) to (197, 2)} to {(195, 77) to (197, 77)}.

**Figure 1-9 • Array Coordinates for AGL600, AGL600, A3P600, and A3PE600**

## Routing Architecture

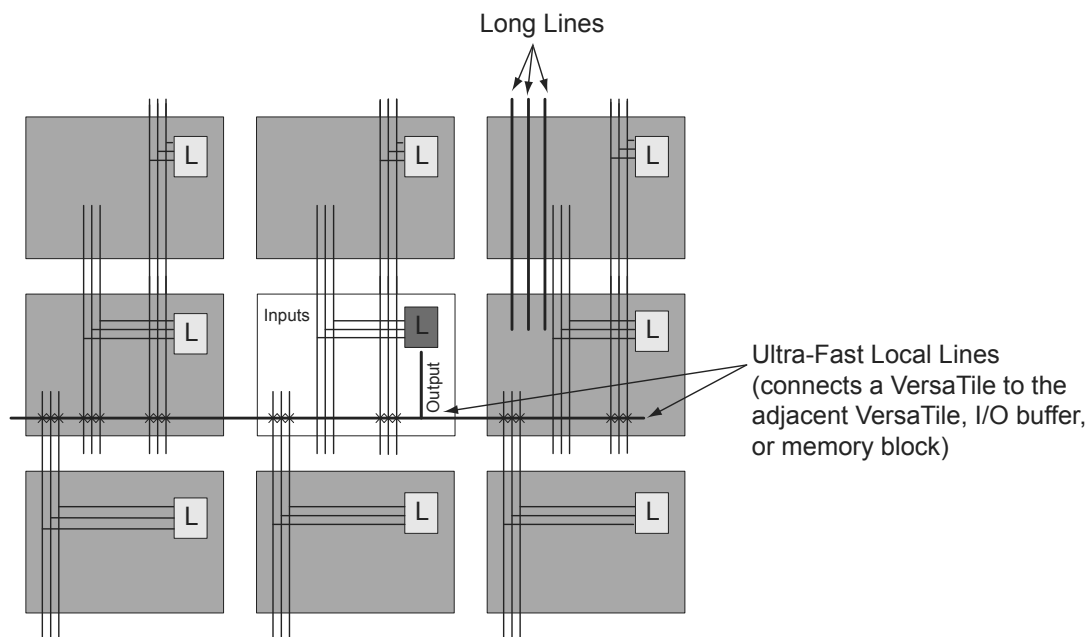
The routing structure of low power flash devices is designed to provide high performance through a flexible four-level hierarchy of routing resources: ultra-fast local resources; efficient long-line resources; high-speed, very-long-line resources; and the high-performance VersaNet networks.

The ultra-fast local resources are dedicated lines that allow the output of each VersaTile to connect directly to every input of the eight surrounding VersaTiles (Figure 1-10). The exception to this is that the SET/CLR input of a VersaTile configured as a D-flip-flop is driven only by the VersaNet global network.

The efficient long-line resources provide routing for longer distances and higher-fanout connections. These resources vary in length (spanning one, two, or four VersaTiles), run both vertically and horizontally, and cover the entire device (Figure 1-11 on page 19). Each VersaTile can drive signals onto the efficient long-line resources, which can access every input of every VersaTile. Routing software automatically inserts active buffers to limit loading effects.

The high-speed, very-long-line resources, which span the entire device with minimal delay, are used to route very long or high-fanout nets: length  $\pm 12$  VersaTiles in the vertical direction and length  $\pm 16$  in the horizontal direction from a given core VersaTile (Figure 1-12 on page 19). Very long lines in low power flash devices have been enhanced over those in previous ProASIC families. This provides a significant performance boost for long-reach signals.

The high-performance VersaNet global networks are low-skew, high-fanout nets that are accessible from external pins or internal logic. These nets are typically used to distribute clocks, resets, and other high-fanout nets requiring minimum skew. The VersaNet networks are implemented as clock trees, and signals can be introduced at any junction. These can be employed hierarchically, with signals accessing every input of every VersaTile. For more details on VersaNets, refer to the "Global Resources in Low Power Flash Devices" section on page 31.



*Note: Input to the core cell for the D-flip-flop set and reset is only available via the VersaNet global network connection.*

**Figure 1-10 • Ultra-Fast Local Lines Connected to the Eight Nearest Neighbors**



During Layout, Designer will assign two of the signals to quadrant global locations.

### Step 3 (optional)

You can also assign the QCLK1\_c and QCLK2\_c nets to quadrant regions using the following PDC commands:

```
assign_local_clock -net QCLK1_c -type quadrant UL
assign_local_clock -net QCLK2_c -type quadrant LL
```

### Step 4

Import this PDC with the netlist and run Compile again. You will see the following in the Compile report:

The following nets have been assigned to a global resource:

Fanout	Type	Name
1536	INT_NET	Net : EN_ALL_c Driver: EN_ALL_pad_CLKINT Source: AUTO PROMOTED
1536	SET/RESET_NET	Net : ACLR_c Driver: ACLR_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK3_c Driver: QCLK3_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : \$1N14 Driver: \$1I5/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N12 Driver: \$1I6/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N10 Driver: \$1I6/Core Source: ESSENTIAL

The following nets have been assigned to a quadrant clock resource using PDC:

Fanout	Type	Name
256	CLK_NET	Net : QCLK1_c Driver: QCLK1_pad_CLKINT Region: quadrant_UL
256	CLK_NET	Net : QCLK2_c Driver: QCLK2_pad_CLKINT Region: quadrant_LL

### Step 5

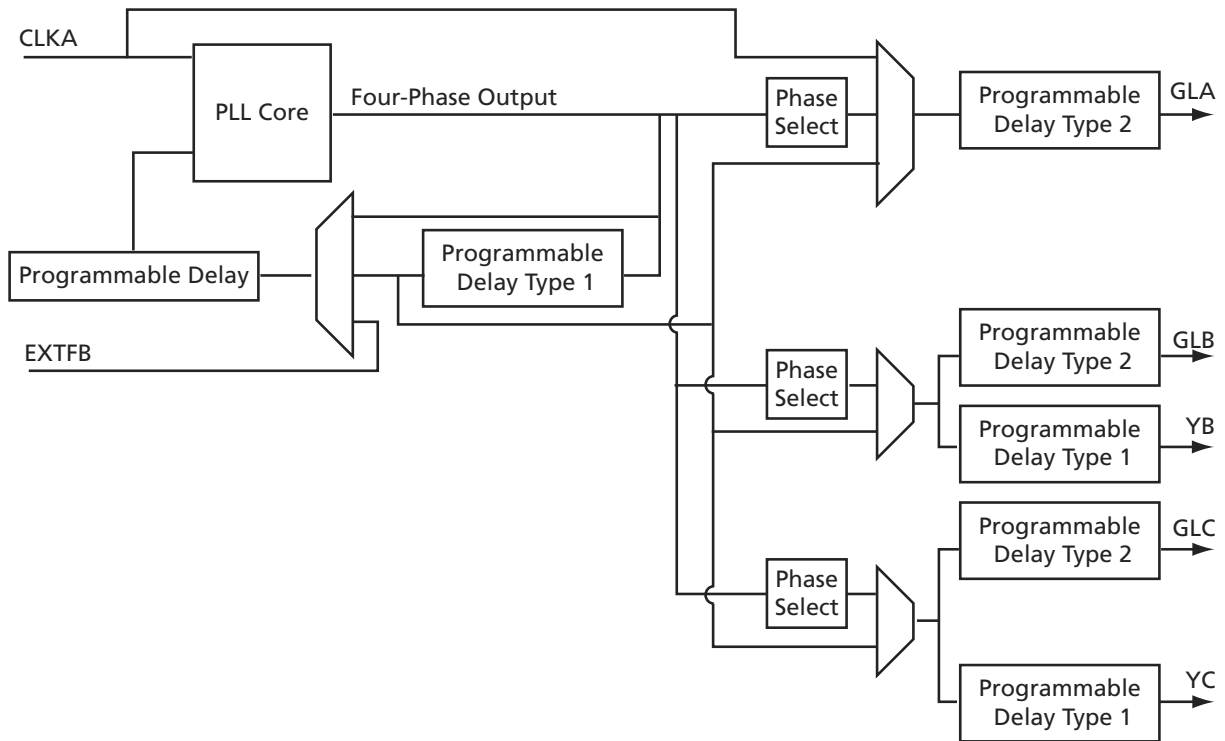
Run Layout.

## Global Management in PLL Design

This section describes the legal global network connections to PLLs in the low power flash devices. For detailed information on using PLLs, refer to "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 61. Microsemi recommends that you use the dedicated global pins to directly drive the reference clock input of the associated PLL for reduced propagation delays and clock distortion. However, low power flash devices offer the flexibility to connect other signals to reference clock inputs. Each PLL is associated with three global networks (Figure 3-5 on page 36). There are some limitations, such as when trying to use the global and PLL at the same time:

- If you use a PLL with only primary output, you can still use the remaining two free global networks.
- If you use three globals associated with a PLL location, you cannot use the PLL on that location.
- If the YB or YC output is used standalone, it will occupy one global, even though this signal does not go to the global network.

SmartGen also allows the user to select the various delays and phase shift values necessary to adjust the phases between the reference clock (CLKA) and the derived clocks (GLA, GLB, GLC, YB, and YC). SmartGen allows the user to select the input clock source. SmartGen automatically instantiates the special macro, PLLINT, when needed.



*Note: Clock divider and clock multiplier blocks are not shown in this figure or in SmartGen. They are automatically configured based on the user's required frequencies.*

**Figure 4-6 • CCC with PLL Block**

## Global Input Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a CCC functional block or to a global / quadrant global network. Figure 4-7 on page 72 and Figure 4-8 on page 72 show the detailed architecture of each global input structure for 30 k gate devices and below, as well as 60 k gate devices and above, respectively. For 60 k gate devices and above (Figure 4-7 on page 72), if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen (not applicable for IGLOO nano and ProASIC3 nano devices), the first and second inputs are considered as paired, and the third input is paired with a regular I/O.

The user then has the choice of selecting one of the two sets to be used as the clock input source to the CCC functional block. There is also the option to allow an internal clock signal to feed the global network or the CCC functional block. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

## Device-Specific Layout

Two kinds of CCCs are offered in low power flash devices: CCCs with integrated PLLs, and CCCs without integrated PLLs (simplified CCCs). Table 4-5 lists the number of CCCs in various devices.

**Table 4-5 • Number of CCCs by Device Size and Package**

Device		Package	CCCs with Integrated PLLs	CCCs without Integrated PLLs (simplified CCC)
ProASIC3	IGLOO			
A3PN010	AGLN010	All	0	2
A3PN015	AGLN015	All	0	2
A3PN020	AGLN020	All	0	2
	AGLN060	CS81	0	6
A3PN060	AGLN060	All other packages	1	5
	AGLN125	CS81	0	6
A3PN125	AGLN125	All other packages	1	5
	AGLN250	CS81	0	6
A3PN250	AGLN250	All other packages	1	5
A3P015	AGL015	All	0	2
A3P030	AGL030/AGLP030	All	0	2
	AGL060/AGLP060	CS121/CS201	0	6
A3P060	AGL060/AGLP060	All other packages	1	5
A3P125	AGL125/AGLP125	All	1	5
A3P250/L	AGL250	All	1	5
A3P400	AGL400	All	1	5
A3P600/L	AGL600	All	1	5
A3P1000/L	AGL1000	All	1	5
A3PE600	AGLE600	PQ208	2	4
A3PE600/L		All other packages	6	0
A3PE1500		PQ208	2	4
A3PE1500		All other packages	6	0
A3PE3000/L		PQ208	2	4
A3PE3000/L	AGLE3000	All other packages	6	0
<b>Fusion Devices</b>				
AFS090		All	1	5
AFS250, M1AFS250		All	1	5
AFS600, M7AFS600, M1AFS600		All	2	4
AFS1500, M1AFS1500		All	2	4

Note: nano 10 k, 15 k, and 20 k offer 6 global MUXes instead of CCCs.

```

wire VCC, GND;

VCC VCC_1_net(.Y(VCC));
GND GND_1_net(.Y(GND));
PLL Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN),
        .GLA(GLA), .LOCK(LOCK), .GLB(), .YB(), .GLC(), .YC(),
        .OADIV0(GND), .OADIV1(GND), .OADIV2(GND), .OADIV3(GND),
        .OADIV4(GND), .OAMUX0(GND), .OAMUX1(GND), .OAMUX2(VCC),
        .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND), .DLYGLA3(GND),
        .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND),
        .OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND),
        .OBMUX2(GND), .DLYYB0(GND), .DLYYB1(GND), .DLYYB2(GND),
        .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND), .DLYGLB1(GND),
        .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND),
        .OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND),
        .OCMUX0(GND), .OCMUX1(GND), .OCMUX2(GND), .DLYYC0(GND),
        .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND),
        .DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND),
        .DLYGLC4(GND), .FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(
VCC), .FINDIV3(GND), .FINDIV4(GND), .FINDIV5(GND),
        .FINDIV6(GND), .FBDIV0(VCC), .FBDIV1(GND), .FBDIV2(VCC),
        .FBDIV3(GND), .FBDIV4(GND), .FBDIV5(GND), .FBDIV6(GND),
        .FBDLY0(GND), .FBDLY1(GND), .FBDLY2(GND), .FBDLY3(GND),
        .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND), .XDLYSEL(GND),
        .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(GND));
defparam Core.VCOFREQUENCY = 33.000;
endmodule

```

The "PLL Configuration Bits Description" section on page 90 provides descriptions of the PLL configuration bits for completeness. The configuration bits are shown as busses only for purposes of illustration. They will actually be broken up into individual pins in compilation libraries and all simulation models. For example, the FBSEL[1:0] bus will actually appear as pins FBSEL1 and FBSEL0. The setting of these select lines for the static PLL configuration is performed by the software and is completely transparent to the user.

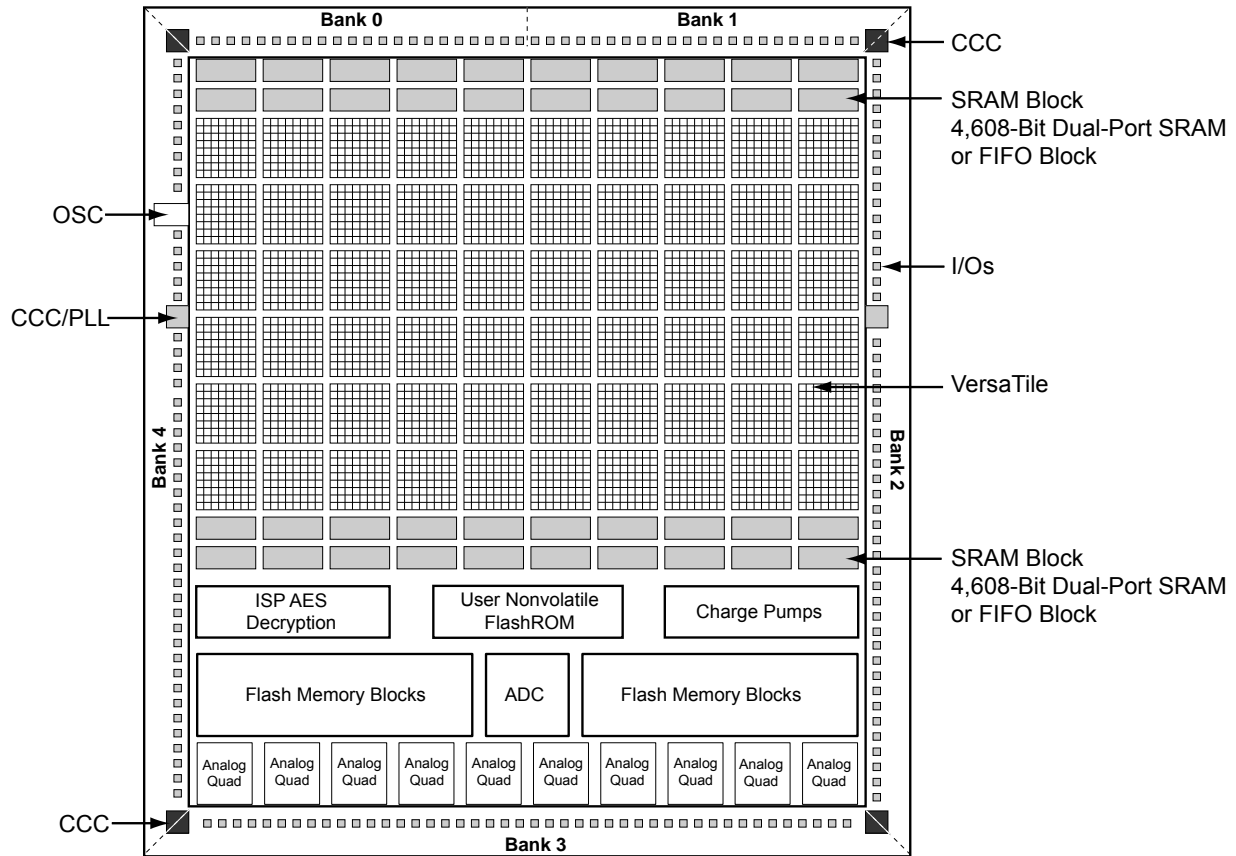
When SmartGen is used to define the configuration that will be shifted in via the serial interface, SmartGen prints out the values of the 81 configuration bits. For ease of use, several configuration bits are automatically inferred by SmartGen when the dynamic PLL core is generated; however, <71:73> (STATASEL, STATBSEL, STATCSEL) and <77:79> (DYNASEL, DYNBSEL, DYNCSEL) depend on the input clock source of the corresponding CCC. Users must first run Layout in Designer to determine the exact setting for these ports. After Layout is complete, generate the "CCC\_Configuration" report by choosing **Tools > Reports > CCC\_Configuration** in the Designer software. Refer to "PLL Configuration Bits Description" on page 90 for descriptions of the PLL configuration bits. For simulation purposes, bits <71:73> and <78:80> are "don't care." Therefore, it is strongly suggested that SmartGen be used to generate the correct configuration bit settings for the dynamic PLL core.

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

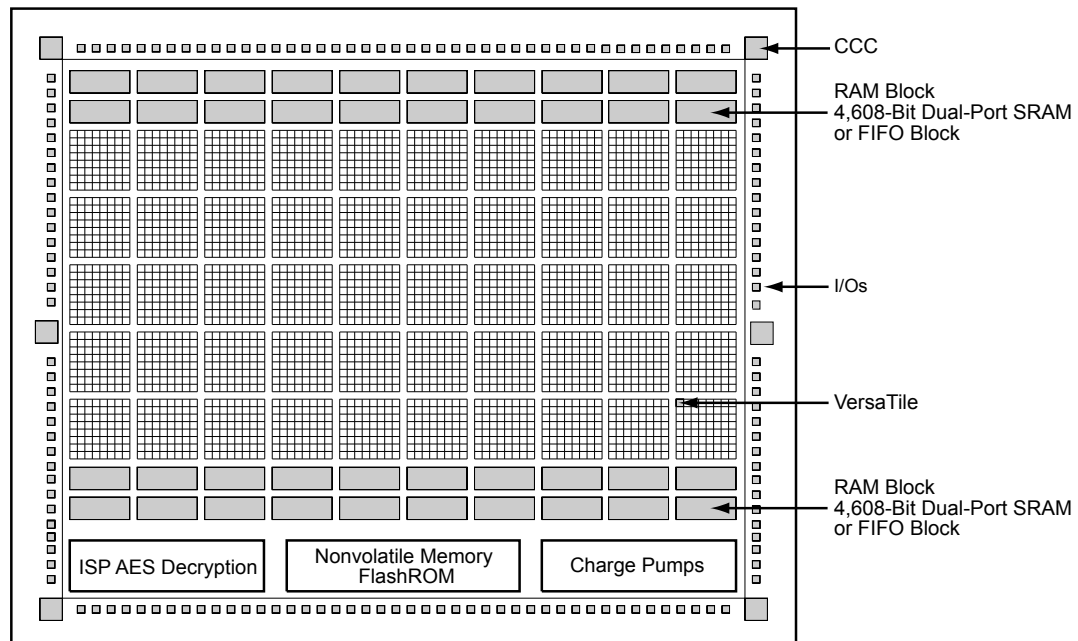
```
*****
Macro Parameters
*****

Name                : dyn_pll_hardio
Family              : ProASIC3E
Output Format        : VERILOG
Type                : Dynamic CCC
Input Freq(MHz)     : 30.000
CLKA Source         : Hardwired I/O
Feedback Delay Value Index : 1
Feedback Mux Select : 1
XDLY Mux Select     : No
Primary Freq(MHz)   : 33.000
Primary PhaseShift  : 0
Primary Delay Value Index : 1
Primary Mux Select  : 4
Secondary1 Freq(MHz) : 40.000
Use GLB             : YES
Use YB              : NO
GLB Delay Value Index : 1
YB Delay Value Index : 1
Secondary1 PhaseShift : 0
Secondary1 Mux Select : 0
Secondary1 Input Freq(MHz) : 40.000
CLKB Source         : Hardwired I/O
Secondary2 Freq(MHz) : 50.000
Use GLC             : YES
Use YC              : NO
GLC Delay Value Index : 1
YC Delay Value Index : 1
Secondary2 PhaseShift : 0
Secondary2 Mux Select : 0
Secondary2 Input Freq(MHz) : 50.000
CLKC Source         : Hardwired I/O

Configuration Bits:
FINDIV[6:0]         0000101
FBDIV[6:0]          0100000
OADIV[4:0]          00100
OBDIV[4:0]          00000
OCDIV[4:0]          00000
OAMUX[2:0]          100
OBMUX[2:0]          000
OCMUX[2:0]          000
FBSEL[1:0]          01
FBDLY[4:0]          00000
XDLYSEL             0
DLYGLA[4:0]         00000
DLYGLB[4:0]         00000
```



**Figure 5-2 • Fusion Device Architecture Overview (AFS600)**



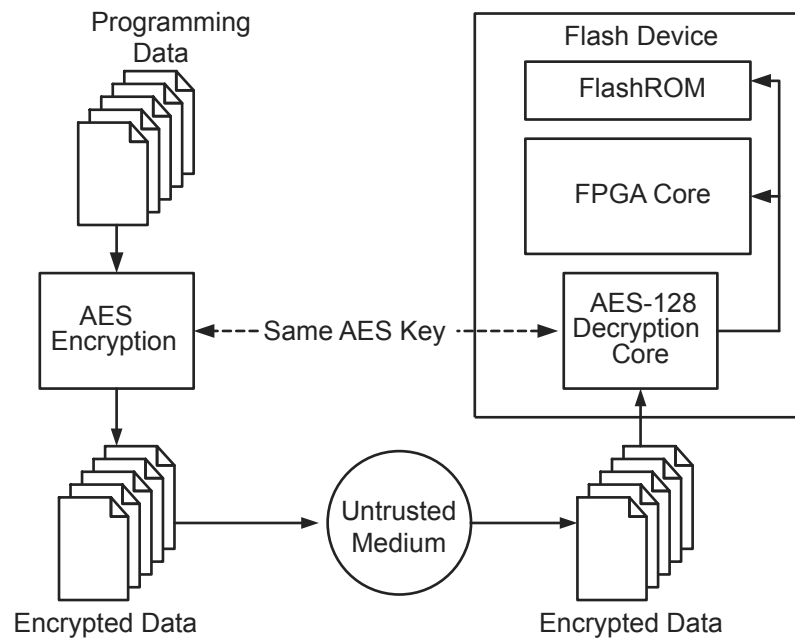
**Figure 5-3 • ProASIC3 and IGLOO Device Architecture**

## FlashROM Security

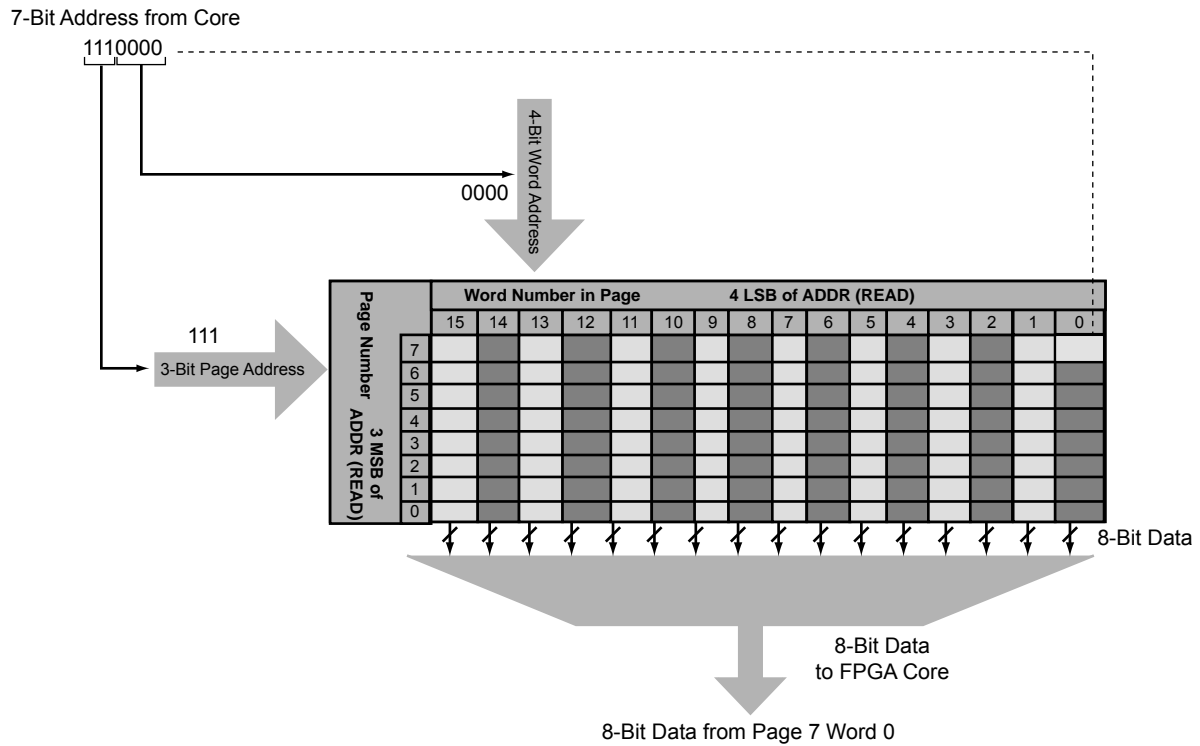
Low power flash devices have an on-chip Advanced Encryption Standard (AES) decryption core, combined with an enhanced version of the Microsemi flash-based lock technology (FlashLock®). Together, they provide unmatched levels of security in a programmable logic device. This security applies to both the FPGA core and FlashROM content. These devices use the 128-bit AES (Rijndael) algorithm to encrypt programming files for secure transmission to the on-chip AES decryption core. The same algorithm is then used to decrypt the programming file. This key size provides approximately  $3.4 \times 10^{38}$  possible 128-bit keys. A computing system that could find a DES key in a second would take approximately 149 trillion years to crack a 128-bit AES key. The 128-bit FlashLock feature in low power flash devices works via a FlashLock security Pass Key mechanism, where the user locks or unlocks the device with a user-defined key. Refer to the "Security in Low Power Flash Devices" section on page 235.

If the device is locked with certain security settings, functions such as device read, write, and erase are disabled. This unique feature helps to protect against invasive and noninvasive attacks. Without the correct Pass Key, access to the FPGA is denied. To gain access to the FPGA, the device first must be unlocked using the correct Pass Key. During programming of the FlashROM or the FPGA core, you can generate the security header programming file, which is used to program the AES key and/or FlashLock Pass Key. The security header programming file can also be generated independently of the FlashROM and FPGA core content. The FlashLock Pass Key is not stored in the FlashROM.

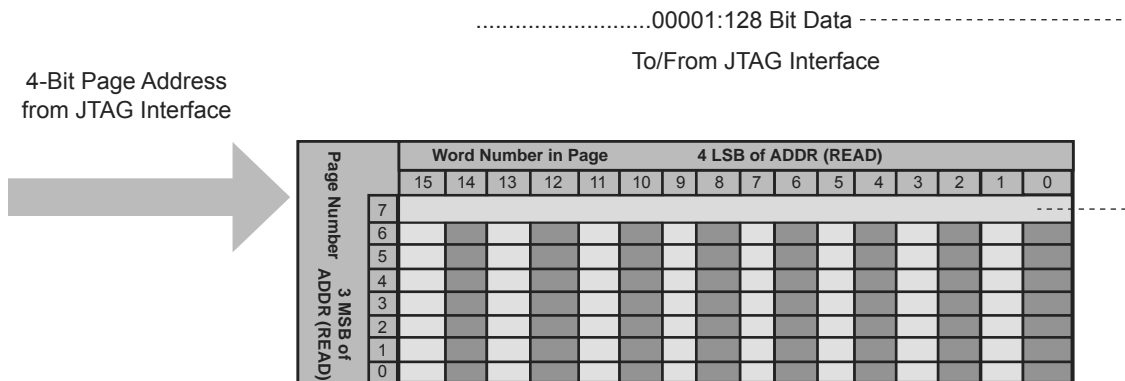
Low power flash devices with AES-based security allow for secure remote field updates over public networks such as the Internet, and ensure that valuable intellectual property (IP) remains out of the hands of IP thieves. Figure 5-5 shows this flow diagram.



**Figure 5-5 • Programming FlashROM Using AES**

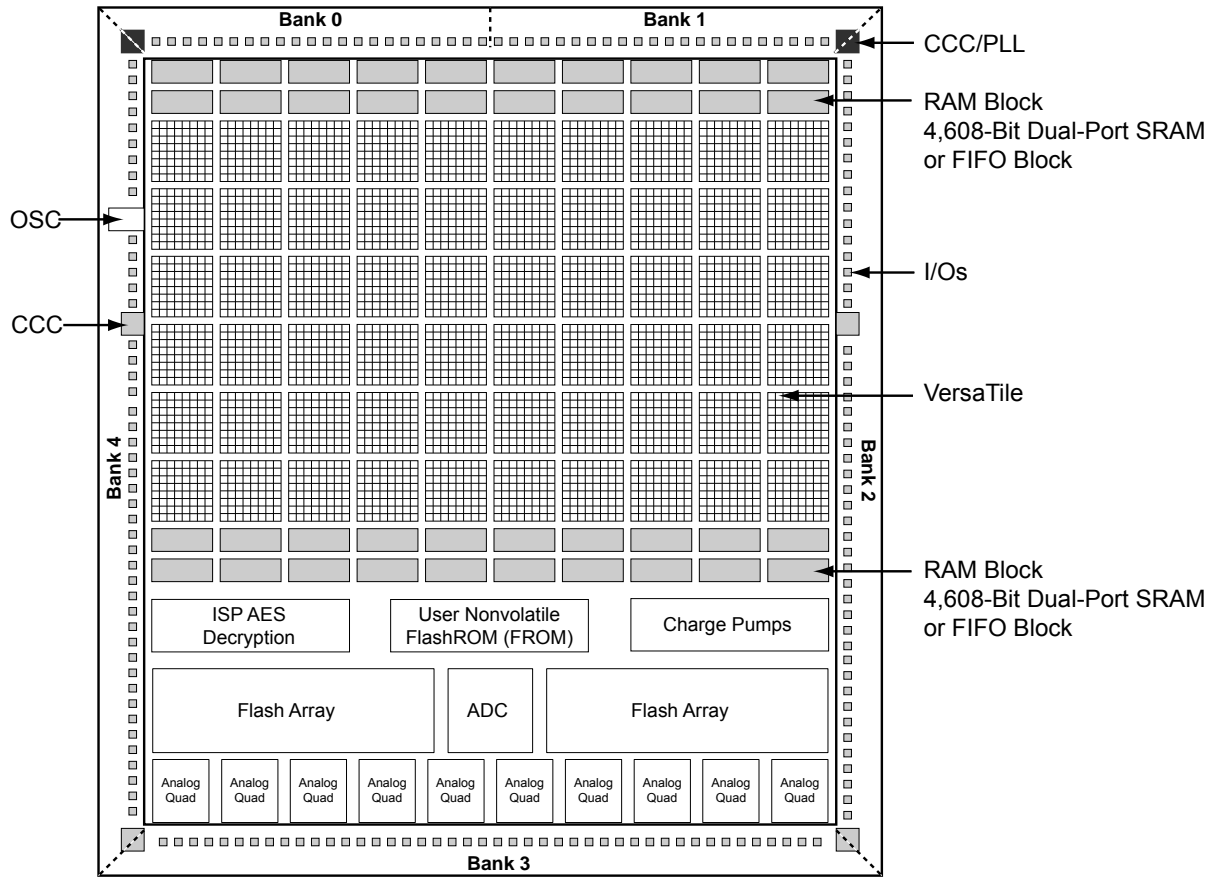


**Figure 5-7 • Accessing FlashROM Using FPGA Core**



**Figure 5-8 • Accessing FlashROM Using JTAG Port**





**Figure 6-2 • Fusion Device Architecture Overview (AFS600)**

- If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
  - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
  - If the clear or preset pins are present, they must have the same polarity.
  - If the clear or preset pins are present, they must be driven by the same signal (net).
3. For single-tile devices (10 k, 15 k, and 20 k): Registers connected to an I/O on the Output and Output Enable pins must have the same clock function (both CLR and CLK are shared among all registers):
    - Both the Output and Output Enable registers must not have an E pin (clock enable).
  4. For dual-tile devices (60 k, 125 k, and 250 k): Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
    - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
    - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a buffer while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

## Weak Pull-Up and Weak Pull-Down Resistors

nano devices support optional weak pull-up and pull-down resistors on each I/O pin. When the I/O is pulled up, it is connected to the  $V_{CCI}$  of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications and when using IGLOO nano devices, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash\*Freeze mode. Refer to "Flash\*Freeze Technology and Low Power Modes" in an applicable FPGA fabric user's guide for more information.

The Flash\*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

## Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic LOW to logic HIGH or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions.

The slew rate can be implemented by using a PDC command (Table 7-5 on page 163), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

Microsemi recommends the high slew rate option to minimize the propagation delay. This high-speed option may introduce noise into the system if appropriate signal integrity measures are not adopted. Selecting a low slew rate reduces this kind of noise but adds some delays in the system. Low slew rate is recommended when bus transients are expected.

## Output Drive

The output buffers of nano devices can provide multiple drive strengths to meet signal integrity requirements. The LVTTTL and LVCMOS (except 1.2 V LVCMOS) standards have selectable drive strengths.

Drive strength should also be selected according to the design requirements and noise immunity of the system.

3. Double-click I/O to open the Create Core window, which is shown in Figure 8-3).
- 

---

**Figure 8-3 • I/O Create Core Window**

As seen in Figure 8-3, there are five tabs to configure the I/O macro: Input Buffers, Output Buffers, Bidirectional Buffers, Tristate Buffers, and DDR.

**Input Buffers**

There are two variations: Regular and Special.

If the **Regular** variation is selected, only the Width (1 to 128) needs to be entered. The default value for Width is 1.

The **Special** variation has Width, Technology, Voltage Level, and Resistor Pull-Up/-Down options (see Figure 8-3). All the I/O standards and supply voltages ( $V_{CCI}$ ) supported for the device family are available for selection.

## Instantiating in HDL code

All the supported I/O macros can be instantiated in the top-level HDL code (refer to the *IGLOO*, *ProASIC3*, *SmartFusion*, and *Fusion Macro Library Guide* for a detailed list of all I/O macros). The following is an example:

```
library ieee;
use ieee.std_logic_1164.all;
library proasic3e;

entity TOP is
    port(IN2, IN1 : in std_logic; OUT1 : out std_logic);
end TOP;

architecture DEF_ARCH of TOP is

    component INBUF_LVCMOS5U
        port(PAD : in std_logic := 'U'; Y : out std_logic);
    end component;

    component INBUF_LVCMOS5
        port(PAD : in std_logic := 'U'; Y : out std_logic);
    end component;

    component OUTBUF_SSTL3_II
        port(D : in std_logic := 'U'; PAD : out std_logic);
    end component;

    Other component ....

    signal x, y, z,.....other signals : std_logic;

begin

    I1 : INBUF_LVCMOS5U
        port map(PAD => IN1, Y => x);
    I2 : INBUF_LVCMOS5
        port map(PAD => IN2, Y => y);
    I3 : OUTBUF_SSTL3_II
        port map(D => z, PAD => OUT1);

    other port mapping...

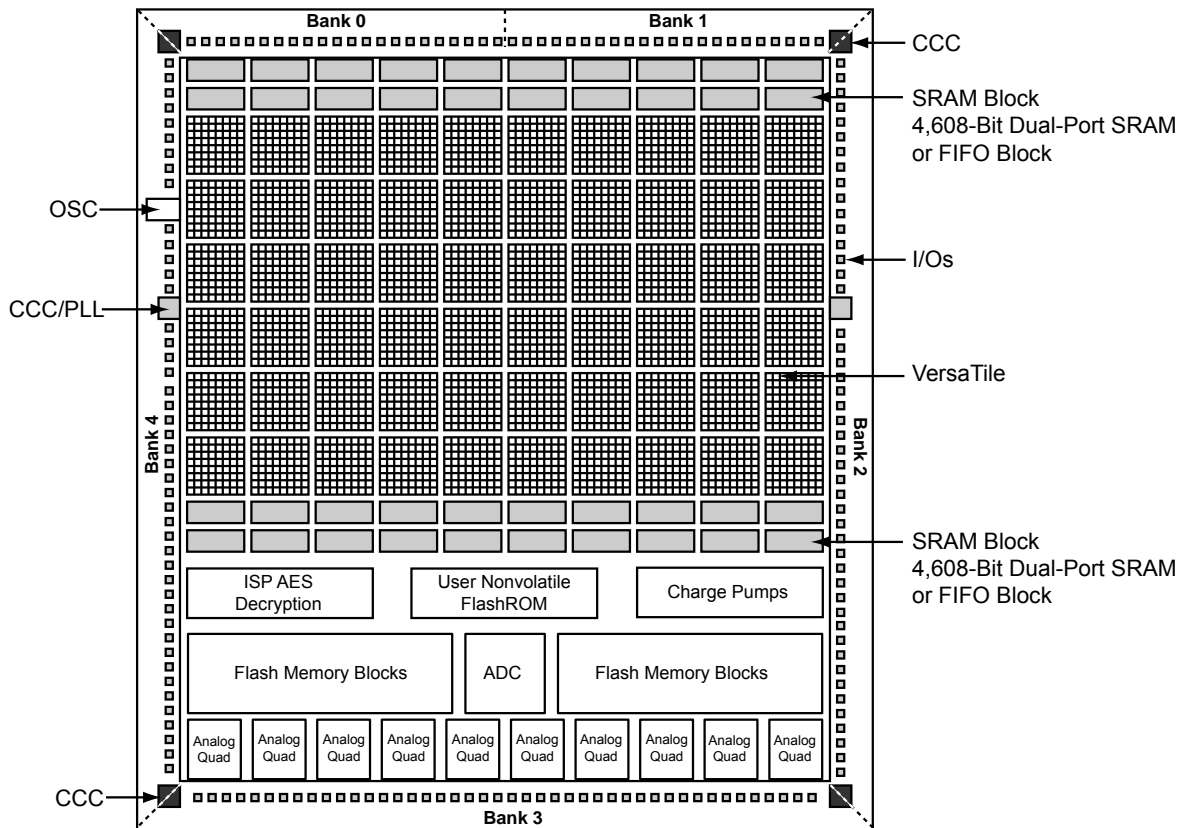
end DEF_ARCH;
```

## Synthesizing the Design

Libero SoC integrates with the Synplify® synthesis tool. Other synthesis tools can also be used with Libero SoC. Refer to the *Libero SoC User's Guide* or Libero online help for details on how to set up the Libero tool profile with synthesis tools from other vendors.

During synthesis, the following rules apply:

- Generic macros:
  - Users can instantiate generic INBUF, OUTBUF, TRIBUF, and BIBUF macros.
  - Synthesis will automatically infer generic I/O macros.
  - The default I/O technology for these macros is LVTTTL.
  - Users will need to use the I/O Attribute Editor in Designer to change the default I/O standard if needed (see Figure 8-6 on page 193).
- Technology-specific I/O macros:
  - Technology-specific I/O macros, such as INBUF\_LVCMOS25 and OUTBUF\_GTL25, can be instantiated in the design. Synthesis will infer these I/O macros in the netlist.



**Figure 11-3 • Block Representation of the AES Decryption Core in a Fusion AFS600 FPGA**

## Security Features

IGLOO and ProASIC3 devices have two entities inside: FlashROM and the FPGA core fabric. Fusion devices contain three entities: FlashROM, FBs, and the FPGA core fabric. The parts can be programmed or updated independently with a STAPL programming file. The programming files can be AES-encrypted or plaintext. This allows maximum flexibility in providing security to the entire device. Refer to the "Programming Flash Devices" section on page 221 for information on the FlashROM structure.

Unlike SRAM-based FPGA devices, which require a separate boot PROM to store programming data, low power flash devices are nonvolatile, and the secured configuration data is stored in on-chip flash cells that are part of the FPGA fabric. Once programmed, this data is an inherent part of the FPGA array and does not need to be loaded at system power-up. SRAM-based FPGAs load the configuration bitstream upon power-up; therefore, the configuration is exposed and can be read easily.

The built-in FPGA core, FBs, and FlashROM support programming files encrypted with the 128-bit AES (FIPS-192) block ciphers. The AES key is stored in dedicated, on-chip flash memory and can be programmed before the device is shipped to other parties (allowing secure remote field updates).

## Security in ARM-Enabled Low Power Flash Devices

There are slight differences between the regular flash devices and the ARM®-enabled flash devices, which have the M1 and M7 prefix.

The AES key is used by Microsemi and preprogrammed into the device to protect the ARM IP. As a result, the design is encrypted along with the ARM IP, according to the details below.

**Table 11-5 • FlashLock Security Options for Fusion**

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	–	–	–	–
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

For this scenario, generate the programming file as follows:

1. Select only the **Security settings** option, as indicated in Figure 11-14 and Figure 11-15 on page 252. Click **Next**.

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**Figure 11-14 • Programming IGLOO and ProASIC3 Security Settings Only**

Table 11-6 and Table 11-7 show all available options. If you want to implement custom levels, refer to the "Advanced Options" section on page 256 for information on each option and how to set it.

3. When done, click **Finish** to generate the Security Header programming file.

**Table 11-6 • All IGLOO and ProASIC3 Header File Security Options**

Security Option	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	✓	✓	✓
FlashLock only	✓	✓	✓
AES and FlashLock	✓	✓	✓

*Note:* ✓ = options that may be used

**Table 11-7 • All Fusion Header File Security Options**

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / No FlashLock	✓	✓	✓	✓
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

## Generation of Programming Files with AES Encryption— Application 3

This section discusses how to generate design content programming files needed specifically at unsecured or remote locations to program devices with a Security Header (FlashLock Pass Key and AES key) already programmed ("Application 2: Nontrusted Environment—Unsecured Location" section on page 243 and "Application 3: Nontrusted Environment—Field Updates/Upgrades" section on page 244). In this case, the encrypted programming file must correspond to the AES key already programmed into the device. If AES encryption was previously selected to encrypt the FlashROM, FBs, and FPGA array, AES encryption must be set when generating the programming file for them. AES encryption can be applied to the FlashROM only, the FBs only, the FPGA array only, or all. The user must ensure both the FlashLock Pass Key and the AES key match those already programmed to the device(s), and all security settings must match what was previously programmed. Otherwise, the encryption and/or device unlocking will not be recognized when attempting to program the device with the programming file.

The generated programming file will be AES-encrypted.

In this scenario, generate the programming file as follows:

1. Deselect **Security settings** and select the portion of the device to be programmed (Figure 11-17 on page 254). Select **Programming previously secured device(s)**. Click **Next**.

*Note: The settings in this figure are used to show the generation of an AES-encrypted programming file for the FPGA array, FlashROM, and FB contents. One or all locations may be selected for encryption.*

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**Figure 11-17 • Settings to Program a Device Secured with FlashLock and using AES Encryption**

Choose the **High** security level to reprogram devices using both the FlashLock Pass Key and AES key protection (Figure 11-18 on page 255). Enter the AES key and click **Next**.

A device that has already been secured with FlashLock and has an AES key loaded must recognize the AES key to program the device and generate a valid bitstream in authentication. The FlashLock Key is only required to unlock the device and change the security settings.

This is what makes it possible to program in an untrusted environment. The AES key is protected inside the device by the FlashLock Key, so you can only program if you have the correct AES key. In fact, the AES key is not in the programming file either. It is the key used to encrypt the data in the file. The same key previously programmed with the FlashLock Key matches to decrypt the file.

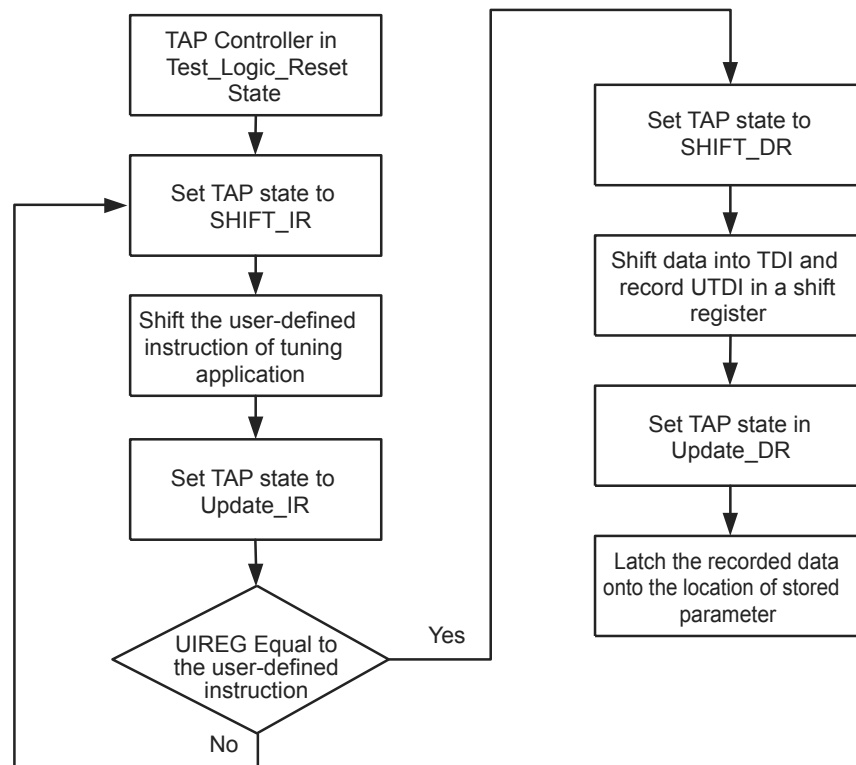
An AES-encrypted file programmed to a device without FlashLock would not be secure, since without FlashLock to protect the AES key, someone could simply reprogram the AES key first, then program with any AES key desired or no AES key at all. This option is therefore not available in the software.



## Fine Tuning

In some applications, design constants or parameters need to be modified after programming the original design. The tuning process can be done using the UJTAG tile without reprogramming the device with new values. If the parameters or constants of a design are stored in distributed registers or embedded SRAM blocks, the new values can be shifted onto the JTAG TAP Controller pins, replacing the old values. The UJTAG tile is used as the “bridge” for data transfer between the JTAG pins and the FPGA VersaTiles or SRAM logic. Figure 16-5 shows a flow chart example for fine-tuning application steps using the UJTAG tile.

In Figure 16-5, the TMS signal sets the TAP Controller state machine to the appropriate states. The flow mainly consists of two steps: a) shifting the defined instruction and b) shifting the new data. If the target parameter is constantly used in the design, the new data can be shifted into a temporary shift register from UTDI. The UDRSH output of UJTAG can be used as a shift-enable signal, and UDRCK is the shift clock to the shift register. Once the shift process is completed and the TAP Controller state is moved to the Update\_DR state, the UDRUPD output of the UJTAG can latch the new parameter value from the temporary register into a permanent location. This avoids any interruption or malfunctioning during the serial shift of the new value.



**Figure 16-5 • Flow Chart Example of Fine-Tuning an Application Using UJTAG**